

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (currently amended)      A leadframe for use in the assembly of integrated circuit chips, comprising:
  - a base metal structure having an adherent layer of nickel covering said base metal;
  - an adherent film of palladium on said nickel layer; and
  - an adherent layer of palladium on said palladium film, selectively covering areas of said leadframe suitable for bonding wire attachment and solder attachment, wherein said film of palladium is sufficiently thin that the surface of said leadframe not covered by said layer of palladium comprises nickel and nickel oxide as well as palladium.
2. (original)    The leadframe according to Claim 1 wherein said base metal is selected from a group consisting of copper, copper alloy, aluminum, iron-nickel alloy, brass, or invar.
3. (original)    The leadframe according to Claim 1 wherein said nickel layer has a thickness in the range from approximately 1 to 3  $\mu\text{m}$ .
4. (original)    The leadframe according to Claim 1 wherein said nickel layer is a stack consisting of a nickel layer in the thickness range from about 30 to 50 nm, plated onto said base metal, followed by a palladium/nickel layer in the thickness range from about 30 to 50 nm, followed by a nickel layer in the thickness range from about 1.0 to 3.0  $\mu\text{m}$ .
5. (original)    The leadframe according to Claim 1 wherein said palladium film has a thickness from about 1 to 5 nm.
6. (original)    The leadframe according to Claim 1 wherein said palladium layer has a thickness from about 70 to 90 nm.
7. (canceled)
8. (currently amended)    ~~The leadframe according to Claim 1 wherein~~ A leadframe for use in the assembly of integrated circuit chips, comprising:

a base metal structure having an adherent layer of nickel covering said base metal;

an adherent film of palladium on said nickel layer; and

an adherent layer of palladium on said palladium film, selectively covering areas of said leadframe suitable for bonding wire attachment and solder attachment said palladium layer provides visual distinction to the areas covered by said layer over the areas of said palladium film uncovered by said palladium layer.

9. (original) The leadframe according to Claim 1 wherein said base metal has a thickness between about 100 and 250  $\mu\text{m}$ .

10. (original) The leadframe according to Claim 1 wherein said solder attachment comprises materials selected from a group consisting of tin/lead, tin/indium, tin/silver, tin/bismuth, tin/copper, tin/silver/copper, and conductive adhesive compounds.

11. (original) The leadframe according to Claim 10 wherein said solder layer has a reflow temperature compatible with wire bonding temperatures and molding temperatures.

12 – 23. (canceled)

24. (currently amended) A semiconductor device, comprising:

a leadframe, comprising:

a film of palladium on said leadframe;

a layer of palladium covering portions of said film of palladium; and

a layer of nickel on said leadframe onto which said film of palladium is deposited, wherein said film of palladium is sufficiently thin that the surface of said leadframe not covered by said layer of palladium comprises nickel and nickel oxide as well as palladium.